



MOCVD Workshop

Metal Organic Chemical Vapor Deposition: Growth, Application, and Analysis

12-4:30 pm April 5th, 2016

Paul G. Allen Bldg Annex, 101X Auditorium
Stanford University Campus

12:00-12:30pm: Refreshments and registration

12:30-12:40pm: Welcome. *Prof. Roger T. Howe, Faculty Director of the Stanford Nanofabrication Facility and William E. Ayer Professor of Electrical Engineering.*

12:40-1:10pm: MOCVD growth of III-V&III-N nanostructures, thin films and heterostructures. *Dr. Xiaoping Xu, Stanford Nanofabrication Facility, Stanford University*

1:10-1:50pm: III-V on silicon for 300mm IC applications. *Dr. Maxim Kelman, Sr. Technology Manager, AIXTRON SE.*

1:50-2:30pm: Emerging GaN-on-Si MEMS: Sensors, Microfabrication, and Interface Materials. *Prof. Debbie G. Senesky, Extreme Environment Microsystems Lab, Stanford University.*

2:30-3:00pm: Break

3:00-3:40pm: Implementation of DUV lasers for high Al content in GaN power devices and DUV LED's and Yield optimization in LED manufacturing by introducing PL based defect control. *Torsten Stoll, product marketing manager MCBU, Nanometrics Inc.*

3:40-4:20pm: Non-contact Metrology for Compound Semiconductors.
Dr. Mark Benjamin, Leighton Electronics, Inc.

Register [here](#) or

